

Art Unit: 2800

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1. (Previously Presented) An SRAM comprising:  
a substrate;  
an insulating film formed on the substrate, said insulating film having a protrusion;  
a pair of cross-coupled driver transistors formed over the substrate;  
a pair of access transistors;  
a pair of bit lines electrically connected to the cross-coupled driver transistors through the access transistors, respectively; and  
a word line electrically connected to the pair of access transistors,  
wherein at least one of the cross-coupled driver transistors comprises a crystalline semiconductor film formed on the insulating film, said crystalline semiconductor film having a mono-domain region in which a channel formation region is formed, and  
wherein said crystalline semiconductor film comprises a source region and a drain region, and a metallic silicide is formed on the surface of said source region and said drain region.

2. (Original) The SRAM according to claim 1 wherein said mono-domain region includes substantially no grain boundary.

3. (Original) The SRAM according to claim 1 wherein any grain boundary included in said mono-domain region is electrically inactive.

7. (Previously Presented) The SRAM comprising:  
a substrate;  
an insulating film formed on the substrate, said insulating film having a protrusion;  
a pair of cross-coupled driver transistors formed over the substrate;  
a pair of access transistors;  
a pair of bit lines electrically connected to the cross-coupled driver transistors through the access transistors, respectively; and  
a word line electrically connected to the pair of access transistors,

wherein at least one of the cross-coupled driver transistors comprises a crystalline semiconductor film formed on the insulating film, said crystalline semiconductor film having a mono-domain region in which a channel formation region is formed,

wherein said crystalline semiconductor film comprises a source region and a drain region, and a metallic silicide is formed on the surface of said source region and said drain region, and

wherein a crystallization direction of said crystalline semiconductor film is substantially in parallel with a major surface of the substrate.

8. (Original) The SRAM according to claim 7 wherein said mono-domain region includes substantially no grain boundary.

9. (Original) The SRAM according to claim 7 wherein any grain boundary included in said mono-domain region is electrically inactive.

10. (Previously Presented) An SRAM comprising:

a substrate;

an insulating film formed on the substrate, said insulating film having a protrusion;

a pair of cross-coupled driver transistors formed over the substrate;

a pair of access transistors;

a pair of bit lines electrically connected to the cross-coupled driver transistors through the access transistors, respectively; and

a word line electrically connected to the pair of access transistors,

wherein at least one of the access transistors comprises a crystalline semiconductor film formed on the insulating film, said crystalline semiconductor film having a mono-domain region in which a channel formation region is formed,

wherein said crystalline semiconductor film comprises a source region and a drain region, and a metallic silicide is formed on the surface of said source region and said drain region, and

wherein a crystallization direction of said crystalline semiconductor film is substantially in parallel with a major surface of the substrate.

11. (Original) The SRAM according to claim 10 wherein said mono-domain region includes substantially no grain boundary.

12. (Original) The SRAM according to claim 10 wherein any grain boundary included in said mono-domain region is electrically inactive.

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19. (Original) A mobile computer comprising the SRAM according to claim 1.
20. (Original) A head-mount display comprising the SRAM according to claim 1.
21. (Original) A motor vehicle navigation comprising the SRAM according to claim 1.
22. (Previously Presented) A mobile phone comprising the SRAM according to claim 1.
23. (Original) A video camera comprising the SRAM according to claim 1.
24. (Original) A projector comprising the SRAM according to claim 1.
31. (Original) A head-mount display comprising the SRAM according to claim 7.
32. (Original) A motor vehicle navigation comprising the SRAM according to claim 7.
33. (Previously Presented) A mobile phone comprising the SRAM according to claim 7.
34. (Original) A video camera comprising the SRAM according to claim 7.

35. (Original) A projector comprising the SRAM according to claim 7.
36. (Original) A mobile computer comprising the SRAM according to claim 7.
37. (Original) A head-mount display comprising the SRAM according to claim 10.
38. (Original) A motor vehicle navigation comprising the SRAM according to claim 10.
39. (Previously Presented) A mobile phone comprising the SRAM according to claim 10.
40. (Original) A video camera comprising the SRAM according to claim 10.
41. (Original) A projector comprising the SRAM according to claim 10.
42. (Original) A mobile computer comprising the SRAM according to claim 10.
55. (New) The SRAM comprising:
- a substrate;
  - an insulating film formed on the substrate, said insulating film having a protrusion;
  - a pair of cross-coupled driver transistors formed over the substrate;
  - a pair of access transistors;
  - a pair of bit lines electrically connected to the cross-coupled driver transistors through the access transistors, respectively; and
  - a word line electrically connected to the pair of access transistors,
- wherein at least one of the cross-coupled driver transistors and the access transistors comprises a crystalline semiconductor film formed on the insulating film, said crystalline semiconductor film having a mono-domain region in which a channel formation region is formed,
- wherein said crystalline semiconductor film comprises a source region and a drain region, and a metallic silicide is formed on the surface of said source region and said drain region, and
- wherein a crystallization direction of said crystalline semiconductor film is substantially in parallel with a major surface of the substrate.

56. (New) The SRAM according to claim 55 wherein said mono-domain region includes substantially no grain boundary.

57. (New) The SRAM according to claim 55 wherein any grain boundary included in said mono-domain region is electrically inactive.

58. (New) A head-mount display comprising the SRAM according to claim 55.

59. (New) A motor vehicle navigation comprising the SRAM according to claim 55.

60. (New) A mobile phone comprising the SRAM according to claim 55.

61. (New) A video camera comprising the SRAM according to claim 55.

62. (New) A projector comprising the SRAM according to claim 55.

63. (New) A mobile computer comprising the SRAM according to claim 55.